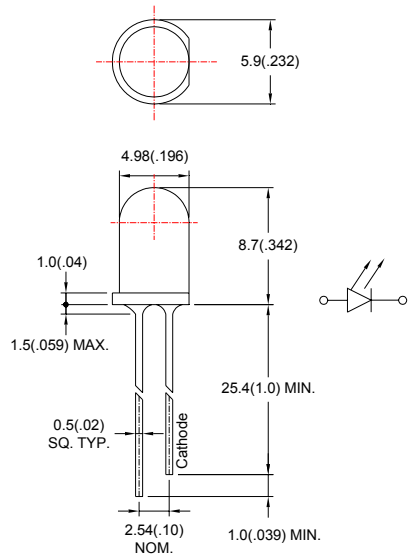
Features:

1. Chip material: AlGaInP/GaAS
2. Emitted color : Super Yellow
3. Lens Appearance : Yellow Diffused
4. Low power consumption.
5. High efficiency.
6. Versatile mounting on P.C. Board or panel.
7. Low current requirement.
8. 5mm diameter package.
9. This product don't contained restriction substance, compliance RoHS standard.

Applications:

1. TV set
2. Monitor
3. Telephone
4. Computer
5. Circuit board

Package dimensions:



Notes:

1. All dimensions are in millimeters (inches).
2. Tolerance is ±0.25mm (0.01") unless otherwise specified.
3. Lead spacing is measured where the leads emerge from the package.
4. Specifications are subject to change without notice.

Absolute maximum ratings(Ta=25℃)

Parameter	Symbol	Rating	Unit
Power Dissipation	Pd	80	mW
Forward Current	I_F	30	mA
Peak Forward Current*[1]	I_{FP}	150	mA
Reverse Voltage	V_R	5	V
Operating Temperature	Topr	-40℃~85℃	
Storage Temperature	Tstg	-40℃~100℃	
Soldering Temperature	Tsol	260℃max (for 5 seconds)	
Hand Soldering Temperature	Tsol	350℃max(for 3 seconds)	

*[1]Condition for I_{FP} is pulse of 1/10 duty and 0.1msec width.

● Electrical and optical characteristics(Ta=25℃)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	I_F=20mA	-	2.0	2.6	V
Luminous Intensity	Iv	I_F=20mA	-	1400	-	mcd
Reverse Current	I_R	V_R=5V	-	-	100	μA
Peak Wave Length	λp	I_F=20mA	-	590	-	nm
Dominant Wave Length	λd	I_F=20mA	588	-	594	nm
Spectral Line Half-width	Δλ	I_F=20mA	-	15	-	nm
Viewing Angle	$2\theta_{1/2}$	I_F=20mA	-	40	-	deg

● Typical electro-optical characteristics curves

Fig.1 Relative intensity vs. Wavelength

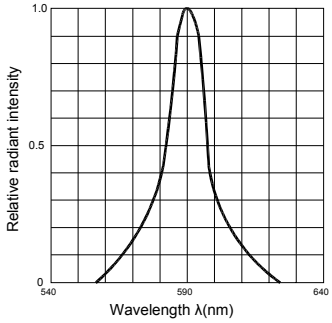


Fig.2 Forward current derating curve vs. Ambient temperature

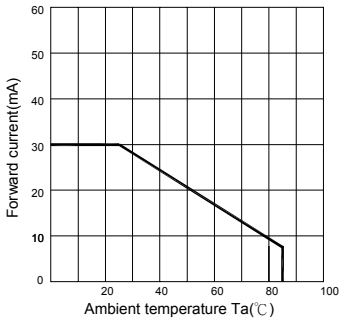


Fig.3 Forward current vs. Forward voltage

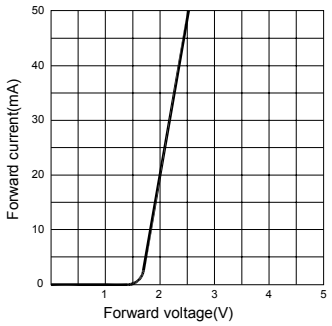


Fig.4 Relative luminous intensity vs. Ambient temperature

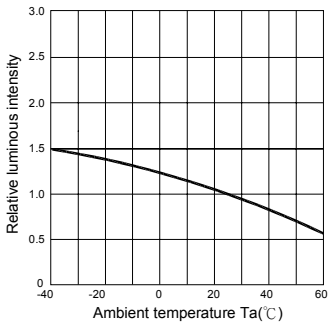


Fig.5 Relative luminous intensity vs. Forward current

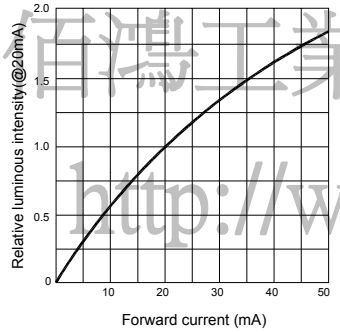
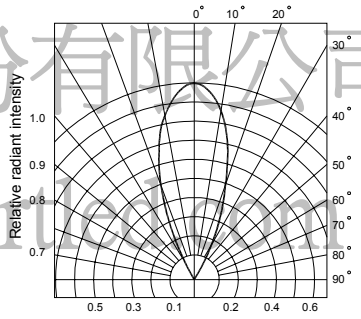


Fig.6 Radiation diagram



● Bin Limits

1. Intensity bin limits (At I_F= 20mA)

Bin Code	Min. (mcd)	Max. (mcd)
U	475	715
V	715	1070
W	1070	1600
X	1600	2400
Y	2400	3700

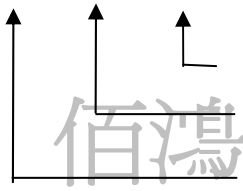
2. Color Bin Limits (At I_F=20mA) : Dominant Wave Length λd(nm)

Bin Code	Min. (nm)	Max. (nm)
5	588	590
6	590	592
7	592	594

3.V_F Bin limits (At I_F=20mA)

Bin Code	Min. (v)	Max. (v)
A	1.6	1.8
B	1.8	2.0
C	2.0	2.2
D	2.2	2.4
E	2.4	2.6

● Bin : x x x



NOTES:1.Tolerance of measurement of luminous intensity. :±15%

2.Tolerance of measurement of dominant wavelength :±1.0nm

3.Tolerance of measurement of forward voltage :±0.05V

● DIP soldering (Wave Soldering)

Preheating : 120℃,within 120~180 sec.
Operation heating : 255℃±5℃ within 5 sec.260℃ (Max)
Gradual Cooling (Avoid quenching).